

## **AMENDMENTS TO THE CLAIMS**

### **Please amend the claims as follows:**

1. (Currently Amended) A method comprising:  
over an area of a substrate, forming a plurality of three dimensional first structures;  
following forming the first structures, conformally introducing a sacrificial material over the area of the substrate including on a top portion and a side portion of the plurality of first structures;  
introducing a second structural material over the sacrificial material;  
exposing a portion of the sacrificial material;  
removing the sacrificial material; and  
wherein removing the sacrificial material comprises suspending the second structural material as a second structure electrically coupled to the first structure.
2. (Canceled)
3. (Previously Presented) The method of claim 1, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
4. (Original) The method of claim 1, prior to introducing the second structural material, further comprising patterning the sacrificial material.
5. (Original) The method of claim 1, wherein the first structural material comprises silicon and the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.
6. (Canceled)
7. (Original) The method of claim 1, wherein patterning the first structures defines a plurality of first areas of the portion of the substrate occupied by the first structures and at least a second area of the portion of the substrate free of the first structures, and introducing the sacrificial material comprises introducing the sacrificial material at least over the second area.

8. (Currently Amended) A method comprising:  
over an area of a surface of a substrate, lithographically patterning a plurality of first structures, the plurality of first structures having a first dimension about the surface of the substrate and a second different dimension;  
following forming the plurality of first structures, conformally introducing a sacrificial material layer over the area of the substrate including on a top portion and a side portion of the plurality of first structures;  
patterning the sacrificial material;  
forming second structures over the sacrificial material;  
removing the sacrificial material; and  
wherein removing the sacrificial material comprises suspending the second structure by the first structure, and wherein the second structure is electrically coupled to the first structure.
9. (Canceled)
10. (Original) The method of claim 8, prior to removing the sacrificial material, further comprising exposing a portion of the sacrificial material.
11. (Previously Presented) The method of claim 10, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
12. (Original) The method of claim 8, wherein the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.

Claims 13-17 (Canceled)